

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

Hyperfast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- Fast switching
- Surface-mountable package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} \leq 130 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	8	Α
Static characte	eristics						
V _F	forward voltage	I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic characteristics							
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; Fig. 7		-	12	18	ns





Hyperfast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	no connection	mb	K — A
2	K	cathode[1]		001aaa020
3	Α	anode		
mb	K	mounting base; connected to cathode	1 3	
			D2PAK (SOT404)	

^[1] It is not possible to connect to pin 2 of the SOT404 package.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC8B-600P	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC8B-600P	BYC8B-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	600	V
V_{RWM}	crest working reverse voltage			-	600	V
V _R	reverse voltage	DC		-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 130 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	8	A
I _{FRM}	repetitive peak forward current	$δ$ = 0.5; t_p = 25 μs; T_{mb} ≤ 130 °C; square-wave pulse		-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		-	91	А
BYC8B-600P	YC8B-600P All information provided in this document is subject to legal disclaimers. © NXP N.V. 2014. All rights reserved					

Hyperfast power diode

Symbol	Parameter	Conditions	Min	Max	Unit
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	А
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

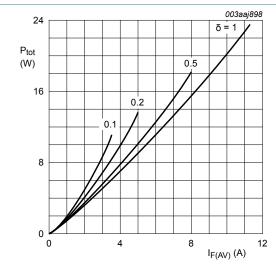


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 1.581 \text{ V; } R_{S} = 0.043 \text{ } \Omega \end{split}$$

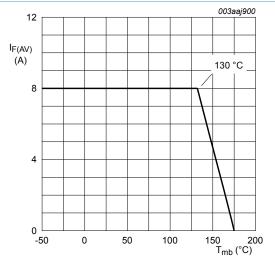


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

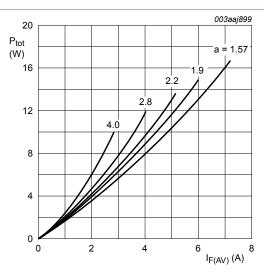


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$

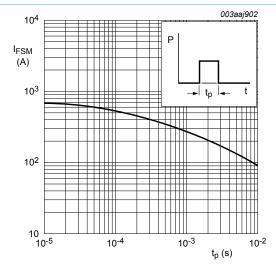


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

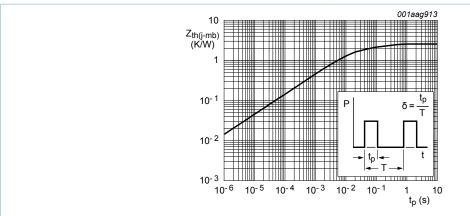


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					,
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.4	-	V
I _R reve	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μA
		V _R = 600 V; T _j = 125 °C	-	-	200	μA
Dynamic cl	haracteristics					
Qr	recovered charge	I_F = 8 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; <u>Fig. 7</u>	-	17	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	90	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 200 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	12	18	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	А
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	6	А

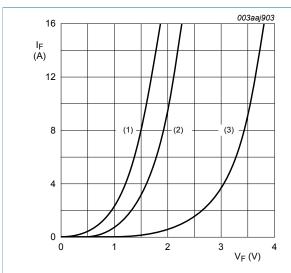
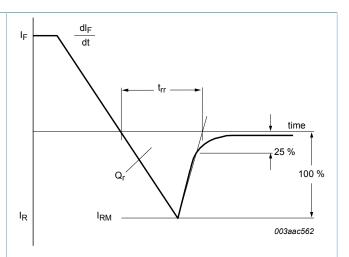


Fig. 6. Forward current as a function of forward voltage

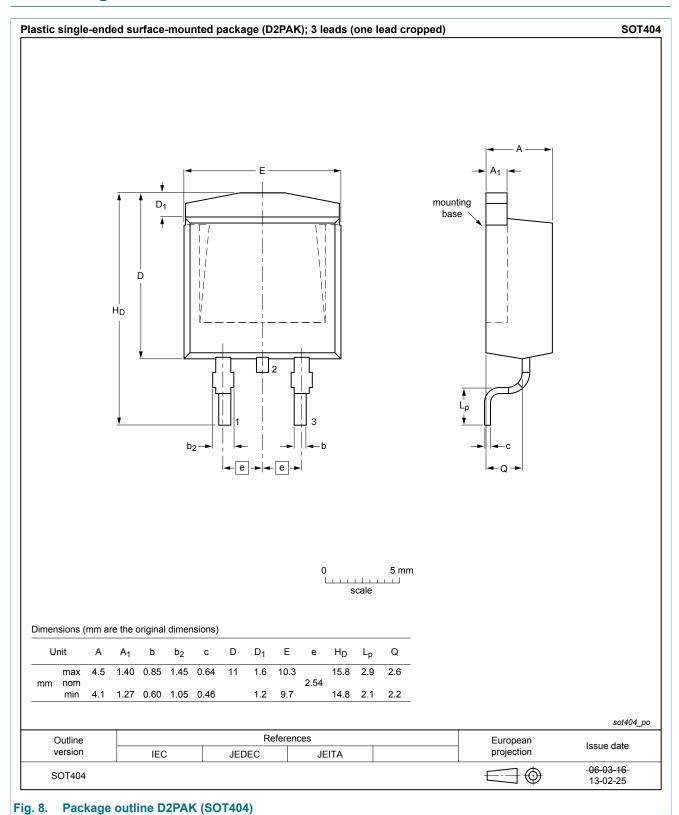
(1) $T_i = 125$ °C; typical values; (2) $T_i = 125$ °C; maximum values; (3) T_i = 25 °C; maximum values; $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$



Reverse recovery definitions; ramp recovery

Hyperfast power diode

11. Package outline



Hyperfast power diode

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Hyperfast power diode

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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	
9	Thermal characteristics	4
10	Characteristics	4
11	Package outline	6
12	Legal information	7
12.1	Data sheet status	7
12.2	Definitions	7
12.3	Disclaimers	7
12.4	Trademarks	8

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